

In the Specification

Page 1, following the title, please insert the following paragraph:

- - This application is a division of U.S. Application No. 09/953,123, filed September 19, 2001, and entitled "Monolithic Three-Dimensional Structures", the disclosure of which is hereby incorporated herein by reference.

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Page 4, please rewrite the page as follows:

- - preferred form of the invention, a first layer of a photoresist material is spun onto a substrate surface and is exposed to a desired pattern corresponding to the shape of the final structure at a corresponding level in the structure. The first layer [film] is not developed after exposure; instead a second layer of photoresist material is deposited on top of the first layer and is also exposed to a pattern at least partially vertically aligned with the first pattern[, and corresponding level of this layer]. Subsequent layers are spun onto the top [surface] surfaces of [the] prior [layer] layers and additional aligned patterns are exposed. If desired, a barrier layer may be provided between successive layers to prevent intermixing. Upon completion of the successive vertically aligned layers defining the structures, the layers are all developed at the same time. This removes the exposed material (in the case of a positive photoresist) leaving the unexposed material behind to form a three-dimensional structure having levels corresponding to the exposed patterns. In the case of a negative photoresist material, the exposed material forms the structure. - -